

RELIABILITY REPORT
FOR
MAX13486EELA+T
PLASTIC ENCAPSULATED DEVICES

February 21, 2013

MAXIM INTEGRATED

160 RIO ROBLES
SAN JOSE, CA 95134

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Conclusion

The MAX13486EELA+T successfully meets the quality and reliability standards required of all Maxim Integrated products. In addition, Maxim Integrated's continuous reliability monitoring program ensures that all outgoing product will continue to meet Maxim Integrated's quality and reliability standards.

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I. Device Description

A. General

The MAX13485E/MAX13486E +5V, half-duplex, $\pm 15\text{kV}$ ESD-protected RS-485 transceivers feature one driver and one receiver. These devices include fail-safe circuitry, guaranteeing a logic-high receiver output when receiver inputs are open or shorted. The receiver outputs a logic-high if all transmitters on a terminated bus are disabled (high impedance). The MAX13485E/MAX13486E include a hot-swap capability to eliminate false transitions on the bus during power-up or live-insertion. The MAX13485E features reduced slew-rate drivers that minimize EMI and reduce reflections caused by improperly terminated cables, allowing error-free transmission up to 500kbps. The MAX13486E driver slew rate is not limited, allowing transmit speeds up to 16Mbps. The MAX13485E/MAX13486E feature a 1/4-unit load receiver input impedance, allowing up to 128 transceivers on the bus. These devices are intended for half-duplex communications. All driver outputs are protected to $\pm 15\text{kV}$ ESD using the Human Body Model. The MAX13485E/MAX13486E are available in 8-pin SO and space-saving 8-pin μDFN packages. The devices operate over the extended -40°C to $+85^{\circ}\text{C}$ temperature range.

II. Manufacturing Information

A. Description/Function:	Half-Duplex RS-485/RS-422 Transceivers in μ DFN
B. Process:	B8
C. Number of Device Transistors:	
D. Fabrication Location:	California or Texas
E. Assembly Location:	Thailand
F. Date of Initial Production:	January 20, 2007

III. Packaging Information

A. Package Type:	8-pin μ DFN
B. Lead Frame:	Substrate
C. Lead Finish:	Gold
D. Die Attach:	Non-conductive
E. Bondwire:	Au (1 mil dia.)
F. Mold Material:	Epoxy with silica filler
G. Assembly Diagram:	#05-9000-2363
H. Flammability Rating:	Class UL94-V0
I. Classification of Moisture Sensitivity per JEDEC standard J-STD-020-C	Level 1
J. Single Layer Theta Ja:	N/A
K. Single Layer Theta Jc:	N/A
L. Multi Layer Theta Ja:	210.2°C/W
M. Multi Layer Theta Jc:	122.1°C/W

IV. Die Information

A. Dimensions:	65 X 43 mils
B. Passivation:	$\text{Si}_3\text{N}_4/\text{SiO}_2$ (Silicon nitride/ Silicon dioxide)
C. Interconnect:	Al/0.5%Cu with Ti/TiN Barrier
D. Backside Metallization:	None
E. Minimum Metal Width:	0.8 microns (as drawn)
F. Minimum Metal Spacing:	0.8 microns (as drawn)
G. Bondpad Dimensions:	
H. Isolation Dielectric:	SiO_2
I. Die Separation Method:	Wafer Saw

V. Quality Assurance Information

- A. Quality Assurance Contacts: Richard Aburano (Manager, Reliability Engineering)
Don Lipps (Manager, Reliability Engineering)
Bryan Preeshl (Vice President of QA)
- B. Outgoing Inspection Level: 0.1% for all electrical parameters guaranteed by the Datasheet.
0.1% For all Visual Defects.
- C. Observed Outgoing Defect Rate: < 50 ppm
- D. Sampling Plan: Mil-Std-105D

VI. Reliability Evaluation

A. Accelerated Life Test

The results of the 135 deg C biased (static) life test are shown in Table 1. Using these results, the Failure Rate (λ) is calculated as follows:

$$\lambda = \frac{1}{\text{MTTF}} = \frac{1.83}{192 \times 4340 \times 45 \times 2} \quad (\text{Chi square value for MTTF upper limit})$$

(where 4340 = Temperature Acceleration factor assuming an activation energy of 0.8eV)

$$\lambda = 24.4 \times 10^{-9}$$

$$\lambda = 24.4 \text{ F.I.T. (60\% confidence level @ 25°C)}$$

The following failure rate represents data collected from Maxim Integrated's reliability monitor program. Maxim Integrated performs quarterly life test monitors on its processes. This data is published in the Reliability Report found at <http://www.maximintegrated.com/qa/reliability/monitor>. Cumulative monitor data for the B8 Process results in a FIT Rate of 0.04 @ 25C and 0.73 @ 55C (0.8 eV, 60% UCL)

B. E.S.D. and Latch-Up Testing (lot TY31DQ001B D/C 0651)

The RU21-1 die type has been found to have all pins able to withstand a HBM transient pulse of +/-2500V per JEDEC JESD22-A114. Latch-Up testing has shown that this device withstands a current of +/-250mA.

Table 1
Reliability Evaluation Test Results

MAX13486EELA+T

TEST ITEM	TEST CONDITION	FAILURE IDENTIFICATION	SAMPLE SIZE	NUMBER OF FAILURES	COMMENTS
Static Life Test (Note 1)	Ta = 135°C Biased Time = 192 hrs.	DC Parameters & functionality	45	0	TY32DQ001B, D/C 0651

Note 1: Life Test Data may represent plastic DIP qualification lots.